

IN THE CLAIMS

This listing of claims replaces all prior versions and listings of the claims in the above-referenced application.

1. (Original) A structure comprising:

a semiconductor light emitting device comprising a light emitting layer disposed between an n-type region and a p-type region, the light emitting layer configured to emit light of a first wavelength; and

a cerium-doped garnet phosphor having a cerium concentration between about 4 mol% and about 8 mol%.

2. (Original) The structure of claim 1 wherein the cerium-doped garnet phosphor has a cerium concentration of about 6 mol%.

3. (Original) The structure of claim 1 wherein the cerium-doped garnet phosphor is  $(Lu_{1-x-y-a-b}Y_xGd_y)_3(Al_{1-z}Ga_z)_5O_{12}:Ce_aPb_b$  wherein  $0 < x < 1$ ,  $0 < y < 1$ ,  $0 < z \leq 0.1$ ,  $0 < a \leq 0.2$  and  $0 < b \leq 0.1$ .

4. (Original) The structure of claim 1 wherein the cerium-doped garnet phosphor is  $Y_3Al_5O_{12}:Ce^{3+}$ .

5. (Original) The structure of claim 1 wherein the cerium-doped garnet phosphor is disposed to absorb light of the first wavelength and capable of absorbing light of the first wavelength and emitting light of a second wavelength.

6. (Original) The structure of claim 5 wherein the first wavelength is blue and the second wavelength ranges from green to yellow.

7. (Original) The structure of claim 5 wherein the cerium-doped garnet phosphor is a first wavelength converting material, the structure further comprising a second wavelength-converting material, wherein the second wavelength-converting material is capable of absorbing light of one of the first wavelength and the second wavelength and emitting light of a third wavelength longer than the second wavelength.

8. (Original) The structure of claim 7 wherein the third wavelength is red.

9. (Original) The structure of claim 7 wherein the second wavelength converting material is one of  $(Ca_{1-x}Sr_x)S:Eu^{2+}$  wherein  $0 < x \leq 1$ ;  $CaS:Eu^{2+}$ ;  $SrS:Eu^{2+}$ ;  $(Sr_{1-x-y}Ba_xCa_y)_2zSi_5-aAl_aN_{8-a}O_a:Eu^{2+}$  wherein  $0 \leq a < 5$ ,  $0 < x \leq 1$ ,  $0 \leq y \leq 1$ , and  $0 < z \leq 1$ ; and  $Sr_2Si_5N_8:Eu^{2+}$ .

10. (Original) The structure of claim 1 wherein the semiconductor light emitting device is a III-nitride light emitting diode.

11. (Original) The structure of claim 1 wherein the cerium-doped garnet phosphor is coated on a top surface and a side surface of the light emitting device.
12. (Original) The structure of claim 1 further comprising:
  - a pair of leads electrically connected to the light emitting device; and
  - a lens disposed over the light emitting device.
13. (Original) The structure of claim 12 wherein the cerium-doped garnet phosphor is dispersed in an encapsulant disposed between the light emitting device and the lens.
14. (Original) The structure of claim 1 wherein the cerium-doped garnet phosphor is spaced apart from the light emitting device.